1 Product profile

1.1 General description

Planar PIN diode in a SOD323 small SMD plastic package.

1.2 Features and benefits

- · High voltage, current controlled
- · RF resistor for RF switches
- · Low diode capacitance
- · Low diode forward resistance
- · Very low series inductance
- AEC-Q101 qualified

1.3 Applications

- · RF attenuators and switches
- Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.



Silicon Pin diode

2 Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode		
2	anode	1 2	₩
		Top view	

3 Ordering information

Table 2. Ordering information

Type number	Package	ре			
	Name	Description	Version		
BAP65-03	-	plastic surface-mounted package; 2 leads	SOD323		

4 Marking

Table 3. Marking

Type number	Marking code
BAP65-03	D3 ^[1]

^[1] The marking bar indicates the cathode (see simplified outline graphic in $\underline{\text{Table 1}}$)

5 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _R	continuous reverse voltage		-	30	V
l _F	continuous forward current		-	100	mA
P _{tot}	total power dissipation	T _{sp} ≤ 90 °C	-	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

6 Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		120	K/W

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7 Characteristics

Table 6. Characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
/ _F	forward voltage	I _F = 50 mA	-	0.9	1.1	V	
R	reverse current	V _R = 20 V	-	-	20	nA	
C_d	diode capacitance	f = 1 MHz (see Figure 1)					
		V _R = 0 V	-	0.65	-	pF	
		V _R = 1 V	-	0.55	0.9	pF	
		V _R = 3 V	-	0.5	0.8	pF	
		V _R = 20 V	-	0.375	-	pF	
r _D	diode forward resistance	f = 100 MHz (see Figure 2)	<u> </u>				
		I _F = 1 mA	-	1	_	Ω	
		I _F = 5 mA	[1]	0.65	0.95	Ω	
		I _F = 10 mA	[1] _	0.56	0.9	Ω	
		I _F = 100 mA	-	0.35	-	Ω	
SL	isolation	V _R = 0 V (see <u>Figure 4</u>)					
		f = 900 MHz	-	10.2	-	dB	
		f = 1800 MHz	-	5.8	-	dB	
		f = 2450 MHz	-	4.1	-	dB	
L _{ins}	insertion loss	See Figure 3.					
		I _F = 1 mA					
		f = 900 MHz	-	0.11	-	dB	
		f = 1800 MHz	-	0.14	-	dB	
		f = 2450 MHz	-	0.18	-	dB	
		I _F = 5 mA					
		f = 900 MHz	-	0.06	-	dB	
		f = 1800 MHz	-	0.10	-	dB	
		f = 2450 MHz	-	0.14	-	dB	
		I _F = 10 mA	_	1			
		f = 900 MHz	-	0.06	-	dB	
		f = 1800 MHz	-	0.1	-	dB	
		f = 2450 MHz	-	0.13	_	dB	
-ins	insertion loss	I _F = 100 mA	1		1		
		f = 900 MHz	-	0.05	_	dB	
		f = 1800 MHz	-	0.1	_	dB	
		f = 2450 MHz	-	0.14	-	dB	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
τι	charge carrier life time	when switched from I _F = 10 mA to I _R = 6 mA; R _L = 100 Ω ; measured at I _R = 3 mA	-	0.17	-	μs
L _S	series inductance	I _F = 100 mA; f = 100 MHz	-	1.5	-	nH

^[1] Guaranteed on AQL basis; inspection level S4, AQL 1.0

Silicon Pin diode

8 Graphical data

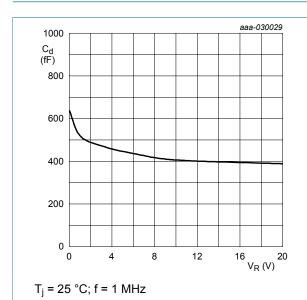
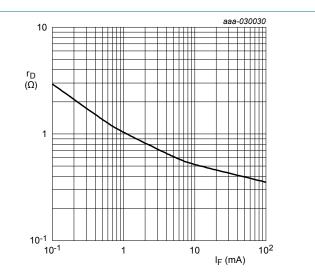
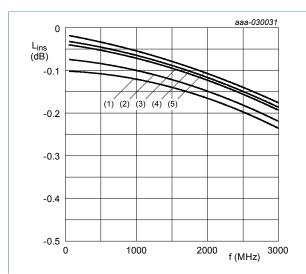


Figure 1. Diode capacitance as a function of reverse voltage (typical values)



 $T_i = 25 \, ^{\circ}C; f = 100 \, MHz.$

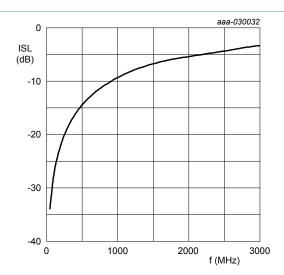
Figure 2. Diode forward resistance as a function of forward current (typical values)



Diode inserted in series with a 50 Ω strip line circuit and biased via the analyzer T-network. T_{amb} = 25 °C.

- (1) $I_F = 0.5 \text{ mA}$
- (2) $I_F = 1 \text{ mA}$
- (3) $I_F = 5 \text{ mA}$
- (4) $I_F = 10 \text{ mA}$
- (5) $I_F = 100 \text{ mA}$

Figure 3. Insertion loss of the diode in on-state as a function of frequency (typical values)



Diode zero-biased and inserted in series with a 50 Ω strip line circuit. T_{amb} = 25 $^{\circ}C.$

Figure 4. Isolation of the diode in off-state as a function of frequency (typical values)

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9 Package outline

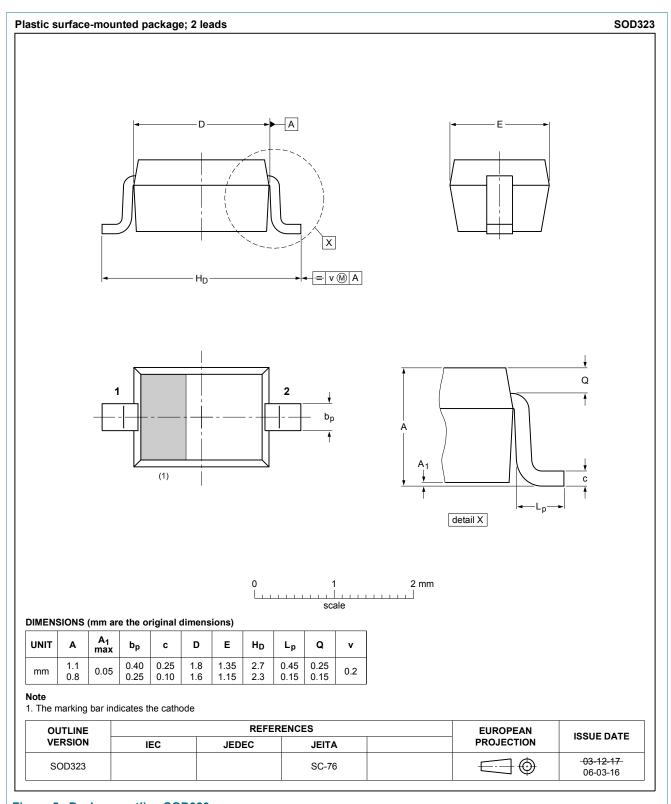


Figure 5. Package outline SOD323

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10 Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BAP65-03 v.5.2	20190128	Product data sheet	-	BAP65-03 v.5.1		
Modifications:	Changed title	to Silicon PIN diode		<u>'</u>		
BAP65-03 v.5.1	20181211	Product data sheet	-	BAP65-03 v.5		
Modifications:		 changed Typ value off L_{ins} at 2450 MHz to 0.18 dB Changed condition I_F on L_Sfrom 10 mA to 100 mA 				
BAP65-03 v.5	20180802	Product data sheet	-	BAP65-03 v.4		
Modifications:		 Section 1.2 "Features and benefits" has been updated. The "Legal information" pages have been updated. 				
BAP65-03 v.4	20040211	Product data sheet	-	BAP65-03 v.3		

Silicon Pin diode

11 Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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